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Ferechteh Hosseini Teherani
David C. Look
David J. Rogers
Editors

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Introduction

The chairs would like to dedicate this volume to the memory of Jeff Nause (CEO of the Atlanta-based ZnO start-up, CERMET). Jeff passed away in the summer of 2012, in the prime of his life, as the result of a tragic accident. Jeff was a frequent contributor at the Photonics West ZnO conference in the past and a dynamo for the ZnO research community as a whole. His passion and enthusiasm for the topic went far beyond the call of duty and his valuable and varied contributions will be sorely missed. As well as his professional contribution, we will also miss Jeff the person: with his friendly disposition and infectious personality he inevitably became a friend to all who collaborated with him.

Ferechteh Hosseini Teherani
David C. Look
David J. Rogers